Session Program

2–4 Jun 2005

6th RD50 - Workshop on Radiation hard semiconductor devices for very high luminosity colliders

Pad Detector Characterization

Physicum campus, University of Helsinki, Finland, 0--E204

Thursday 2 June

13:30

Pad Detector Characterization

Session | **Location:** Helsinki, Finland, 0--E204

13:50–14:10 **Radiation tolerant epitaxial silicon detectors of different thickness**

Speaker
Eckhart Fretwurst

Location
Helsinki, Finland, 0--E204

14:10–14:30
Investigation of voltages and electric fields in silicon radiation detectors using a scanning electron microscope

Speaker
Kari Leinonen

Location
Helsinki, Finland, 0--E204

14:30–14:50 **Irradiation results of MCZ, thinned and epitaxial detectors**

Speaker
Andrea Candelori

Location
Helsinki, Finland, 0--E204

14:50–15:10
Characterization of n and p-type diodes processed on Fz and MCz silicon after irradiation with protons of 24GeV/c and 26 MeV/c and with reactor neutrons

Speaker
Norman Manna

Location
Helsinki, Finland, 0--E204

15:10